

Soitec's engineered substrates for 5G

March 2020






Outline

- 1 What is 5G about?
- 2 5G will drive semiconductor content growth
- 3 Soitec's engineered substrates to enable 5G

5G technology in numbers



 **100x**
Network capacity

(*)



 **10x**
Speed

(*)

 **10x**
Fastest
response time

(*)



 **10x**
Connected
device

(*)



(*) Source: Qualcomm

5G world – beyond smartphones

5G for automotive

Key services

- › Autonomous driving
- › Infotainment
- › Telematics



5G for IoT

Key services

- › Smart everything: home, city, offices, energy
- › Security
- › Healthcare



5G for manufacturing

Key services

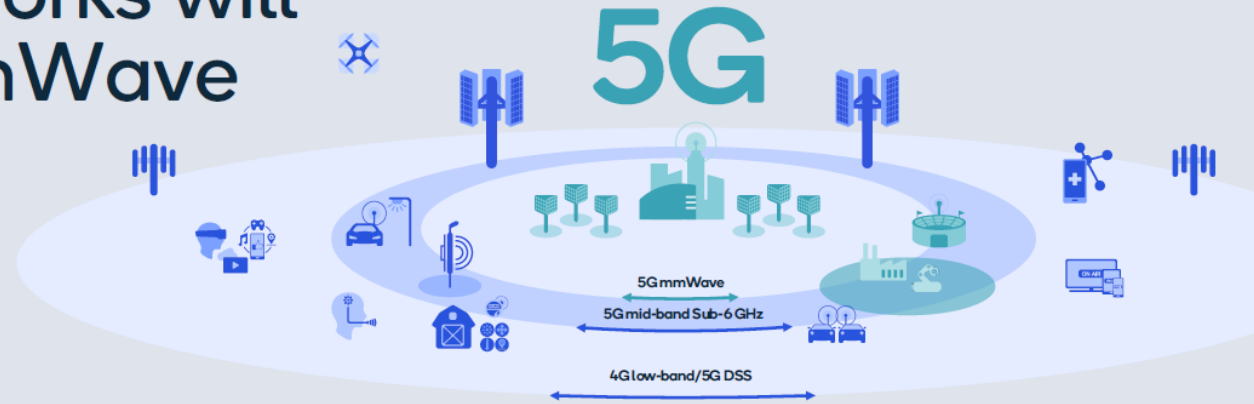
- › Higher automation
- › Higher productivity
- › Higher quality, higher security...



5G – a combination of networks

Leading 5G networks will have Sub-6 + mmWave

Combining coverage, capacity, and performance benefits

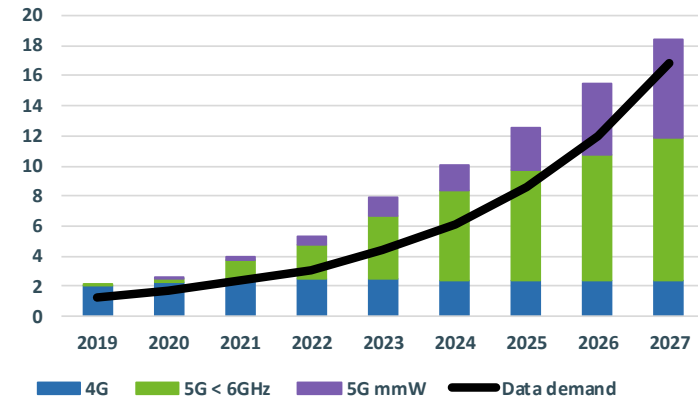


Source: Qualcomm Analyst Day, C. Amon, Nov. 2019

5G – a larger frequency spectrum to manage more data faster

- › 5G new spectrum is 12x larger than overall LTE
- › Will enable network providers to deliver increasing data rate for the next 10 years

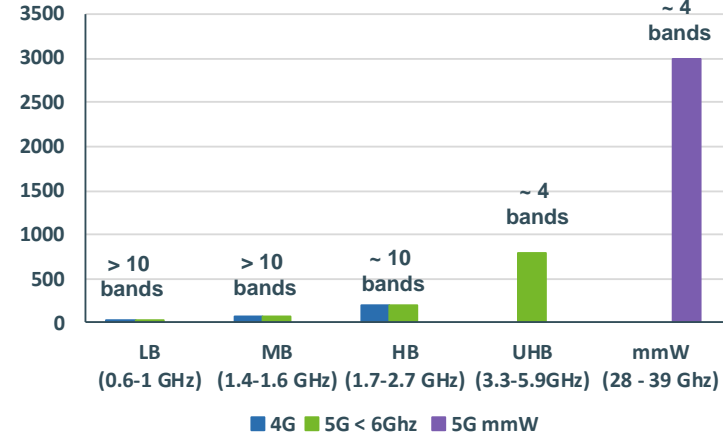
Example: capacity analysis US mobile network



Source: Mobile Experts, Soitec estimates, 2019

max Bandwidth per band (MHz)

5G and LTE spectrum

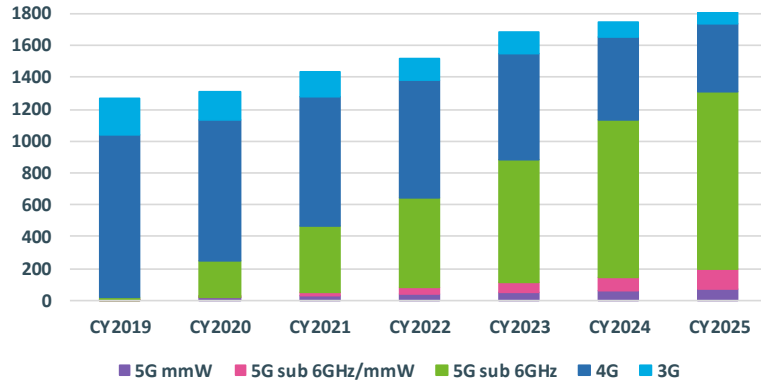


5G massive deployment is starting in 2020

› 50% of smartphones sales in 2023

› around 200Mu in 2020

Smartphone by category (Mu)



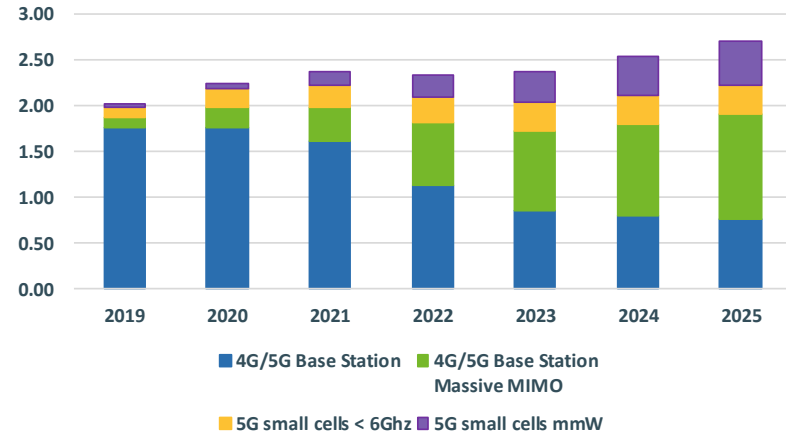
Source: Navian October 2019, Soitec estimates beyond 2023

› 110 5G Operators (Ookla daily update)

› around 200k 5G base stations in 2020

› >55% of worldwide coverage in 2025

Base station and small cells 4G&5G (Mu)



Source: Yole, November 2019

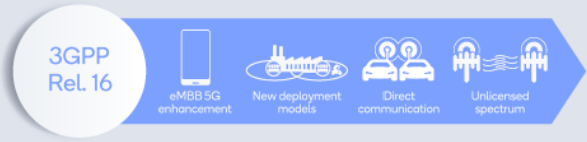
5G roadmap will drive technology and applications for the next decade



5G roadmap extends for 10+ years

Driving innovation to enhance smartphones and transform other industries

Continued innovation for new verticals, deployments, use cases, and spectrum

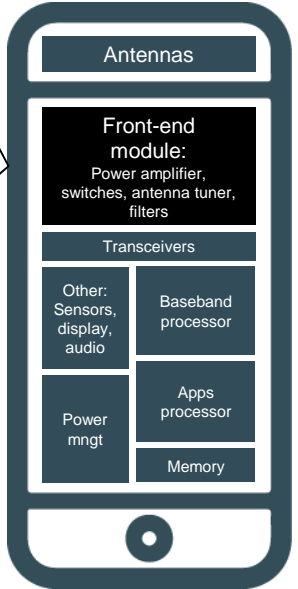
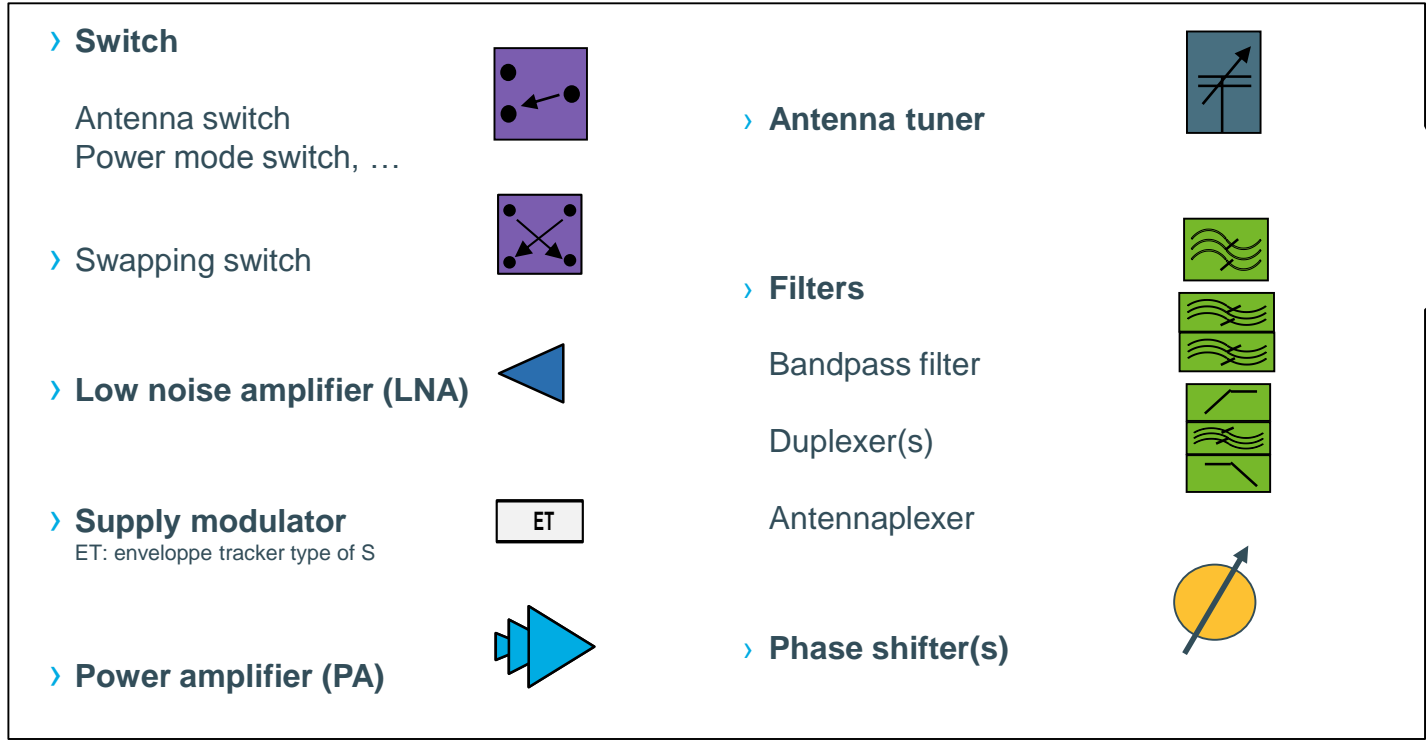


Source: Qualcomm Analyst Day, J. THOMPSON, Nov. 2019

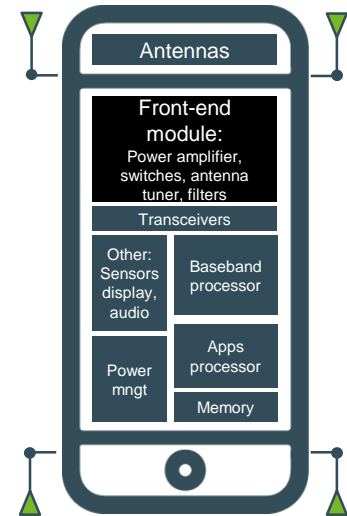
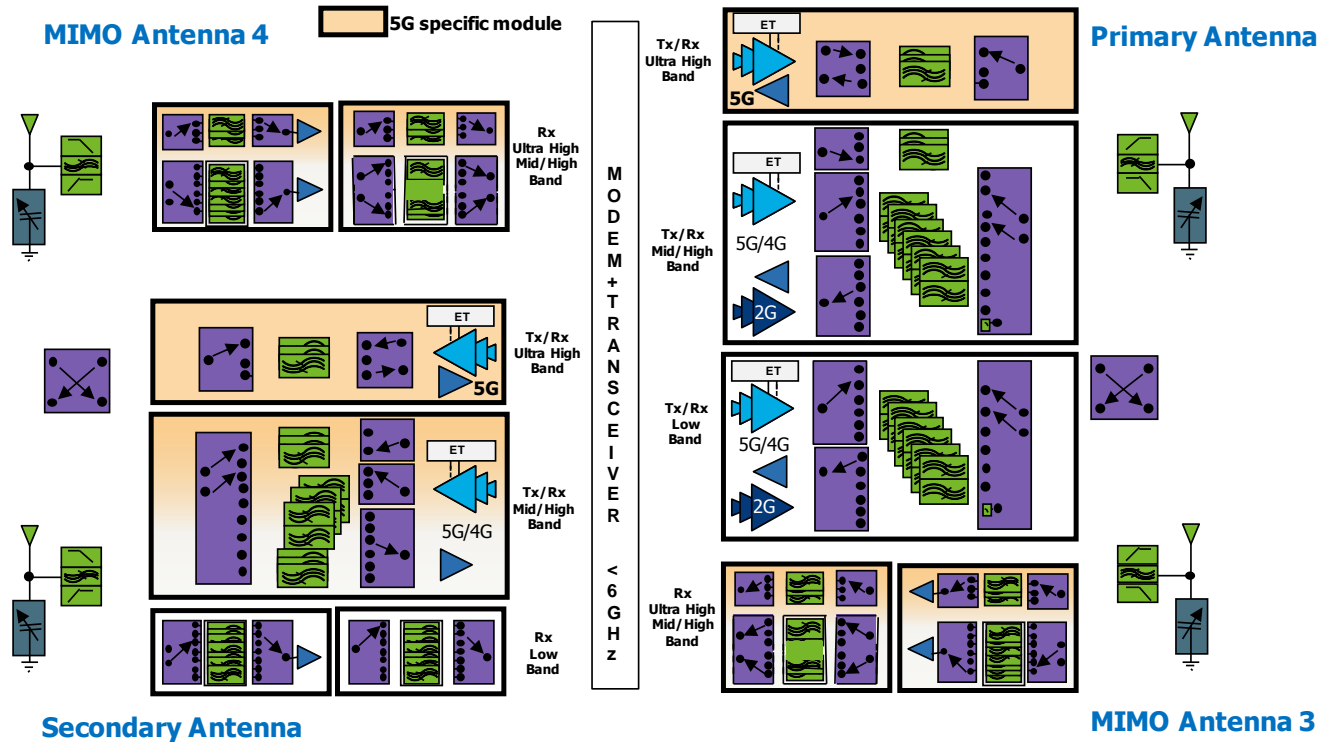
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Front End Module (FEM) blocks – built on Soitec substrates

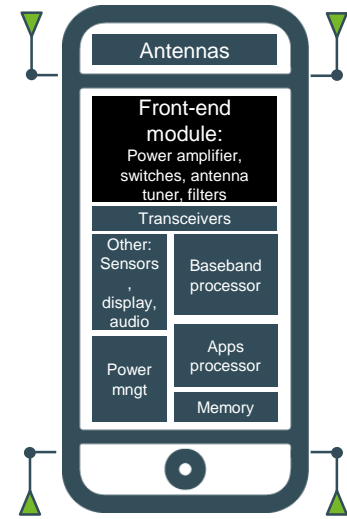
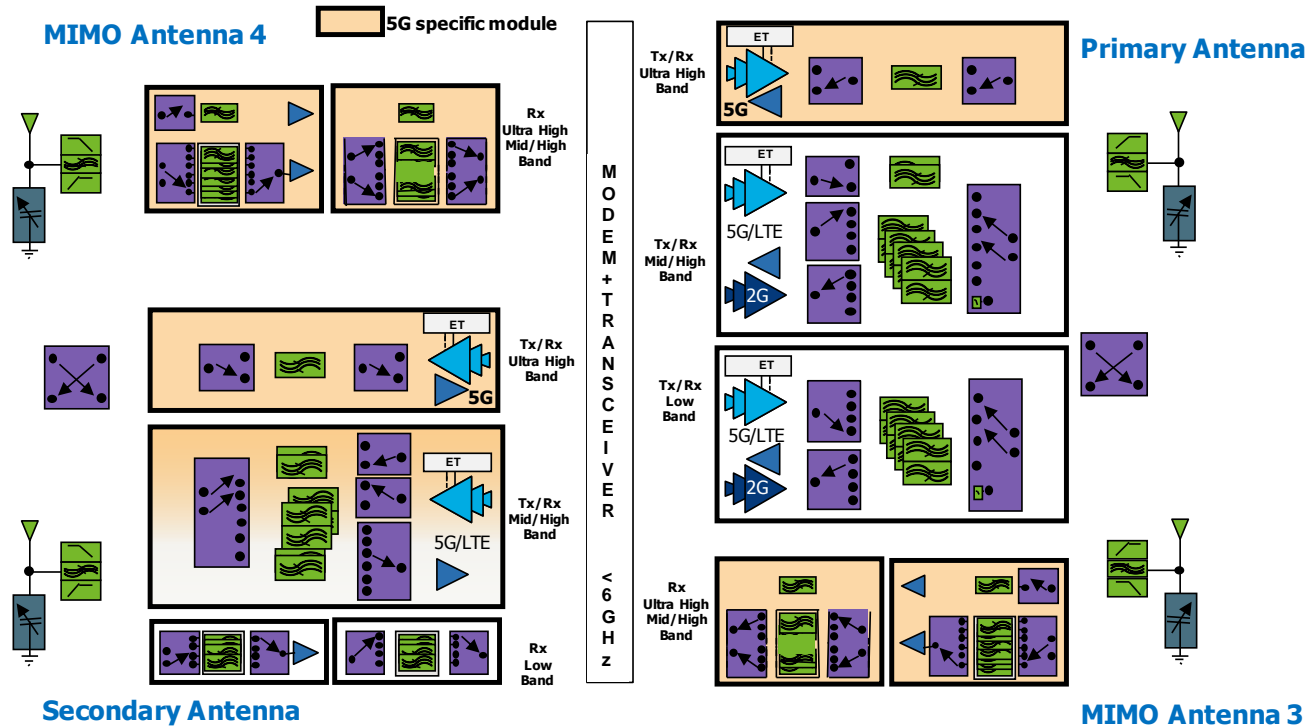


5G sub-6GHz – High end* smartphones: 20% more RF FEM content vs 4G



*: >\$500
30% of smartphones

5G sub-6GHz – Mid end* smartphones: 90% more RF FEM content vs 4G

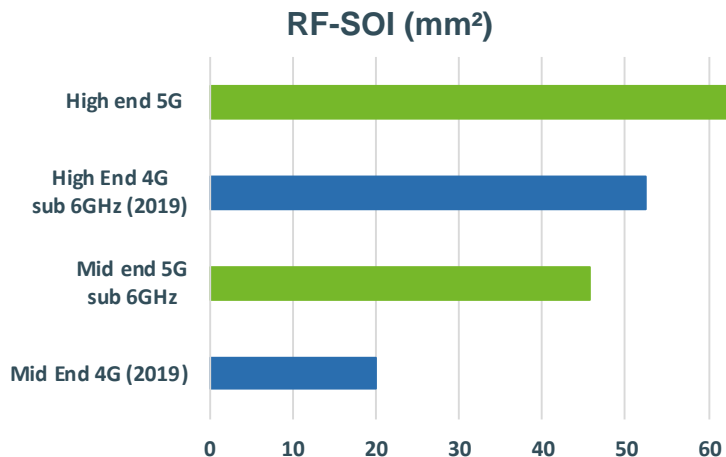


*: \$100 - \$500
50% of smartphones

5G sub-6GHz

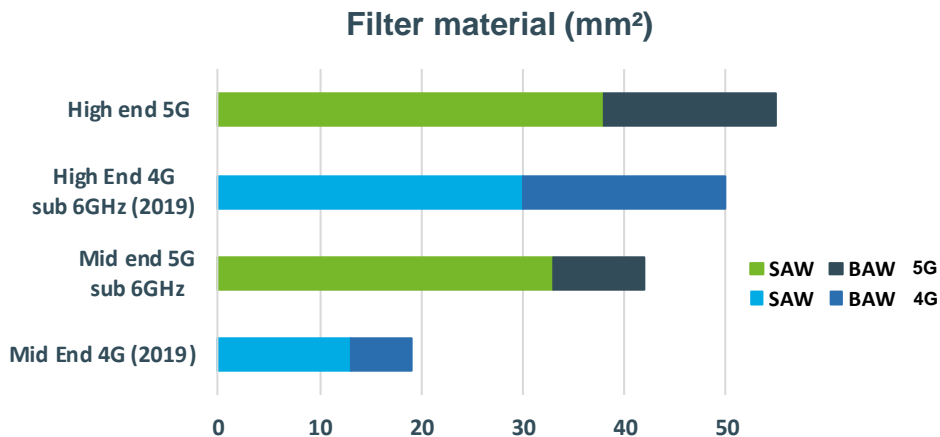
Major content (*) growth for RF-SOI and filters

Average +60% RF-SOI content



Source: System Plus 2019, Soitec estimates

Average +50% filter content



Assumption: new SAW filter generations to take market share over BAW

(*) Mm² are serviceable accessible market

5G mmW module brings additional content to sub-6GHz module

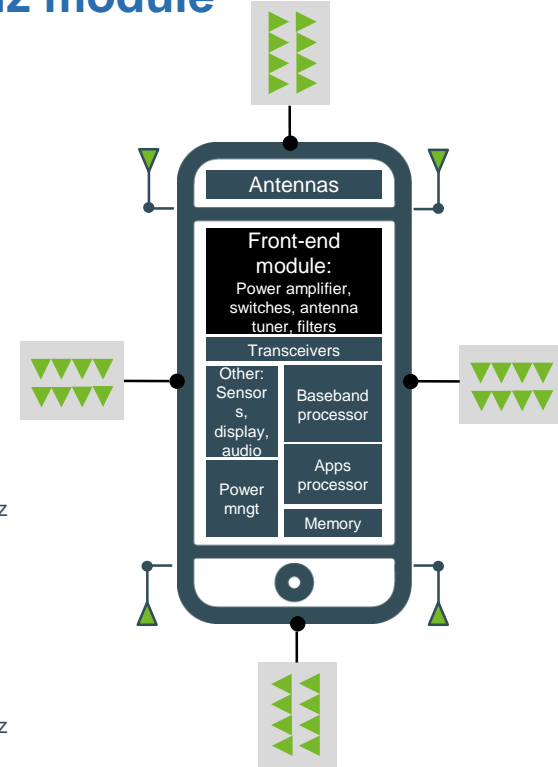
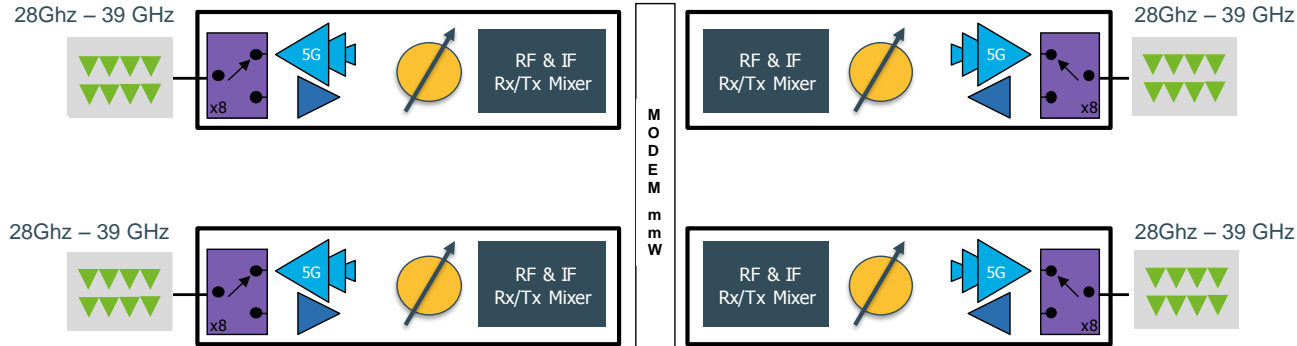
> 5G mmW requires 3 or 4 modules

- › Modules are required so that mmW signal is not blocked by hand nor objects
- › Modules are put on the phone edge



> 28GHz and/or 39GHz bands

- › Starts with one band and will move to two bands

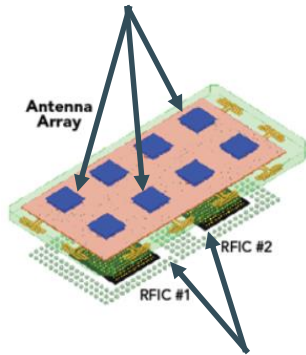


5G mmW smartphone

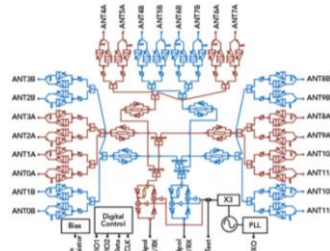
Doubling SOI (*) content vs 5G sub-6GHz smartphone

5G mmW handset modules – in average: 60 mm² of RF-SOI or FD-SOI

8 antennas per module

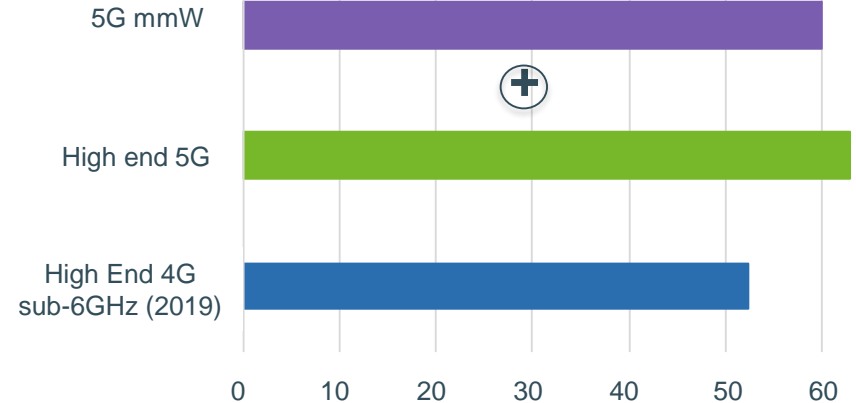


2 transceivers per module, 10mm² each



Transceivers :
PA, LNA, SW,
PLL, Digital
control

RF-SOI or FD-SOI (mm²)



Source: Soitec estimates

(*) : Mm² are serviceable accessible market

Source: Qualcomm IMS 2018, Microwave Journal Dec 2018

Soitec technologies in 3G, 4G, 5G products

From alternative solution for RF switch to standard RF FEM

rfmd



SOI Antenna Switch
(Wi-Fi first introduction)



iPhone 4S



iPhone 5



Galaxy S5



iPhone 8



Mate Pro 30



Galaxy S20

Mate 20 X

2G

3G

LTE

LTE-A

LTE-A-Pro

5G sub-6GHz

5G (sub-6GHz + mmW)

RF-SOI

1

2

7

20

40

50

65

mm²

FD-SOI (*)

2

→ 65

mm²

POI

2 → >25

>25

mm²

Source: System Plus, Soitec estimates

⇒ next generations

(*) either FD-SOI or RF-SOI

Mm² are serviceable accessible market

Soitec “footprint” in mm² across RF standards

Assumptions:

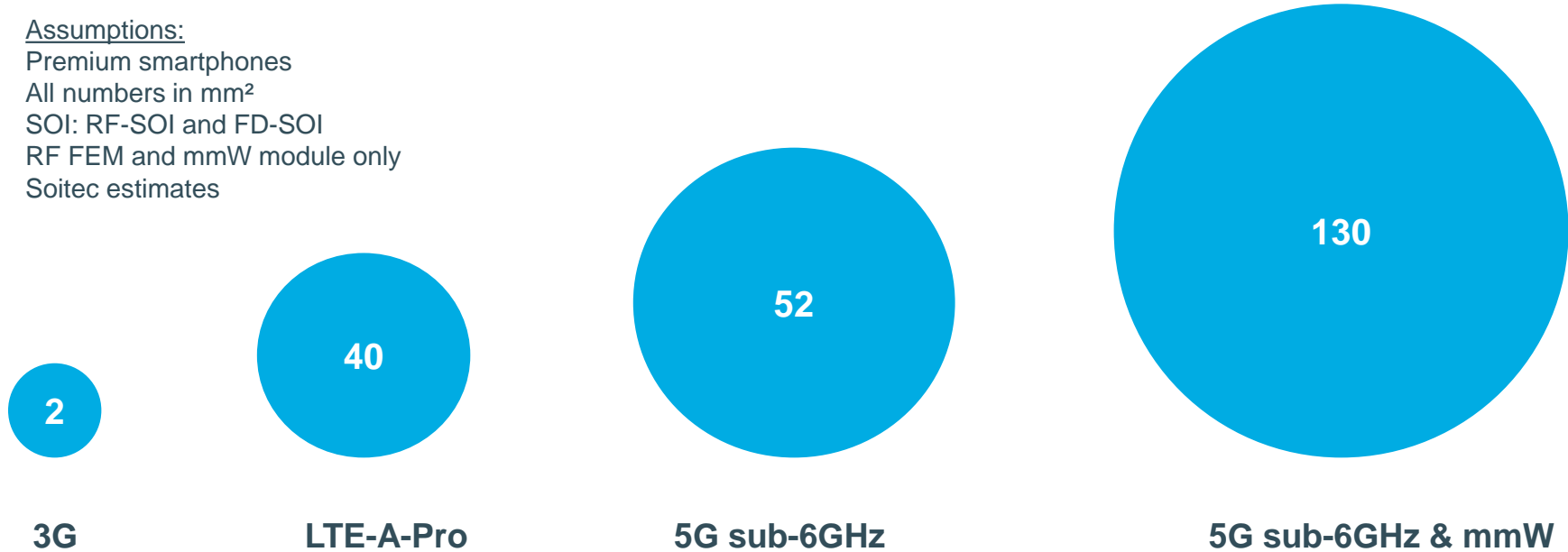
Premium smartphones

All numbers in mm²

SOI: RF-SOI and FD-SOI

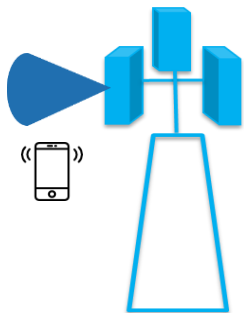
RF FEM and mmW module only

Soitec estimates



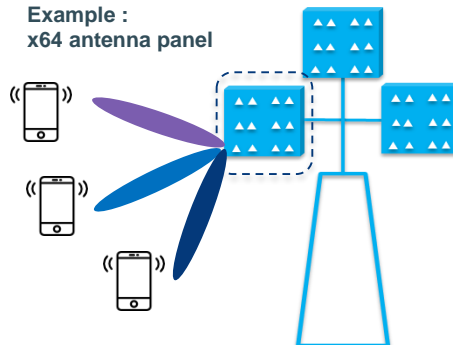
Mm² are serviceable accessible market

5G sub-6GHz base station architecture: major change



> 4G/5G base station

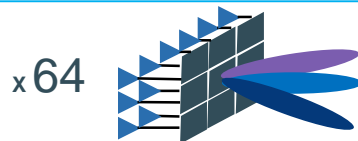
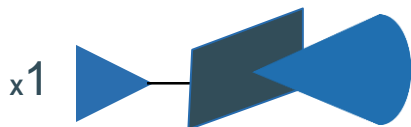
- > Passive antenna system
- > One antenna per panel



Example :
x64 antenna panel

> 5G massive MIMO

- > Active antenna system
- > Cell coverage improved
- > More user served simultaneously



/ 64 > Power per PA
x 64 > FEM (units)

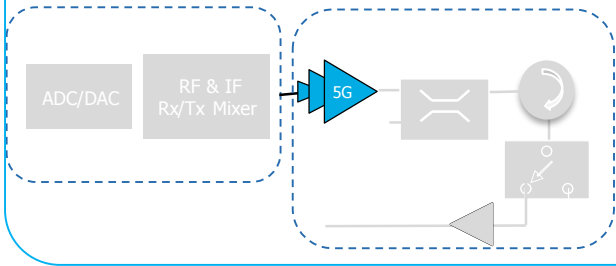
Key challenges require from semiconductor suppliers

- > PA performance stretching above 3.6GHz
- > High power added efficiency
- > Low cost FEM solution
- > Low-power solution

5G sub-6GHz base station: new opportunities for Soitec

x1 transceiver

x1 FEM



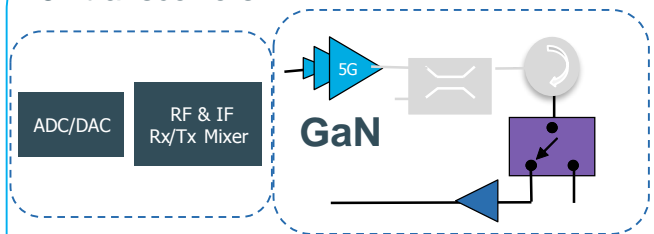
> 5G base station*

- > GaN technology taking market share over LDMOS (laterally-diffused metal-oxide semiconductor)

*Based on 4G architecture

x64 transceivers

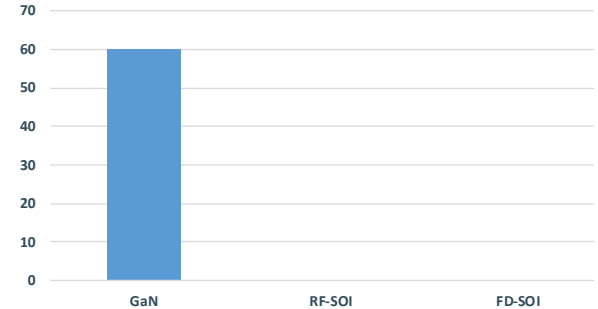
x64 FEM



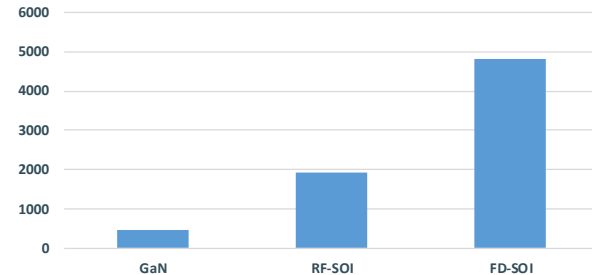
> Massive MIMO 5G

- > Lower power levels allows RF-SOI based switches and LNA integration
- > GaN technology taking market share over LDMOS
- > Low power transceiver with FD-SOI

4G/5G base station content (mm²)



4G/5G base station massive (MIMO) content (mm²)

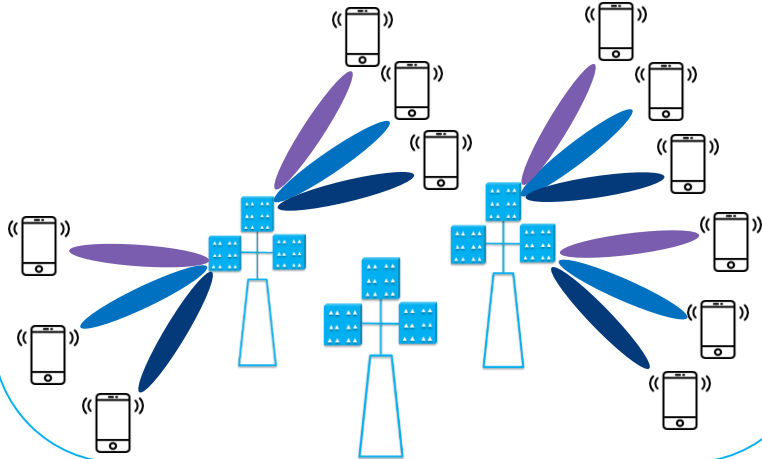


Remark: handset unit is 1,000 larger than base station

5G mmW small cells: new end-to-end architecture

> 5G mmW small cells

- › Ultra high bandwidth
- › Ultra high throughput
- › Increased semiconductor content (until 1024 RF chains)
- › 28-39GHz bands

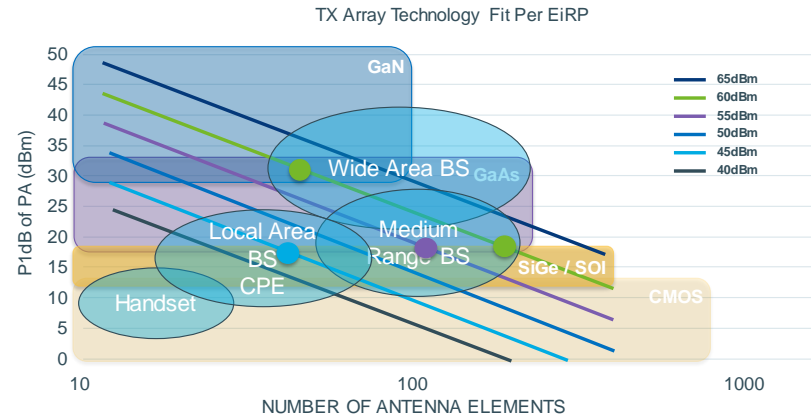


> Multiple type of small cells per market segment

- › Wide, medium, local area coverage

> GaN and SOI cover all cases (ex: wide area small cells)

- › x64 antennas with high power GaN PA
- › x512 antennas with SOI integrated FEM



Source: Analog Devices, 2019

5G small cells mmW: new opportunities for Soitec

X16 chipsets
transceivers

x64 FEM

Low complexity approach

- › FEM in **GaN**
- › Low power transceiver with **FD-SOI**

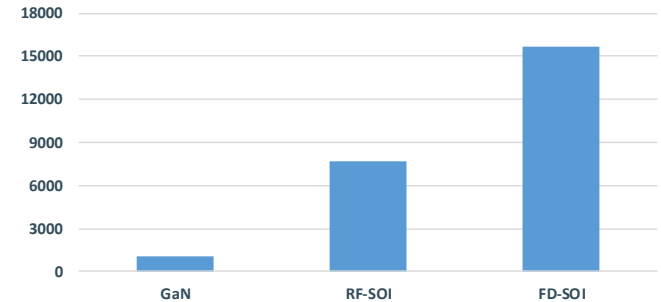
X128 chipsets
transceivers

x512 FEM

High complexity approach

- › FEM in **RF-SOI or FD-SOI**
- › Low power transceiver with **FD-SOI**

5G small cells mmW
content (mm²)



Remark: handset unit is 3,000 larger than small cells

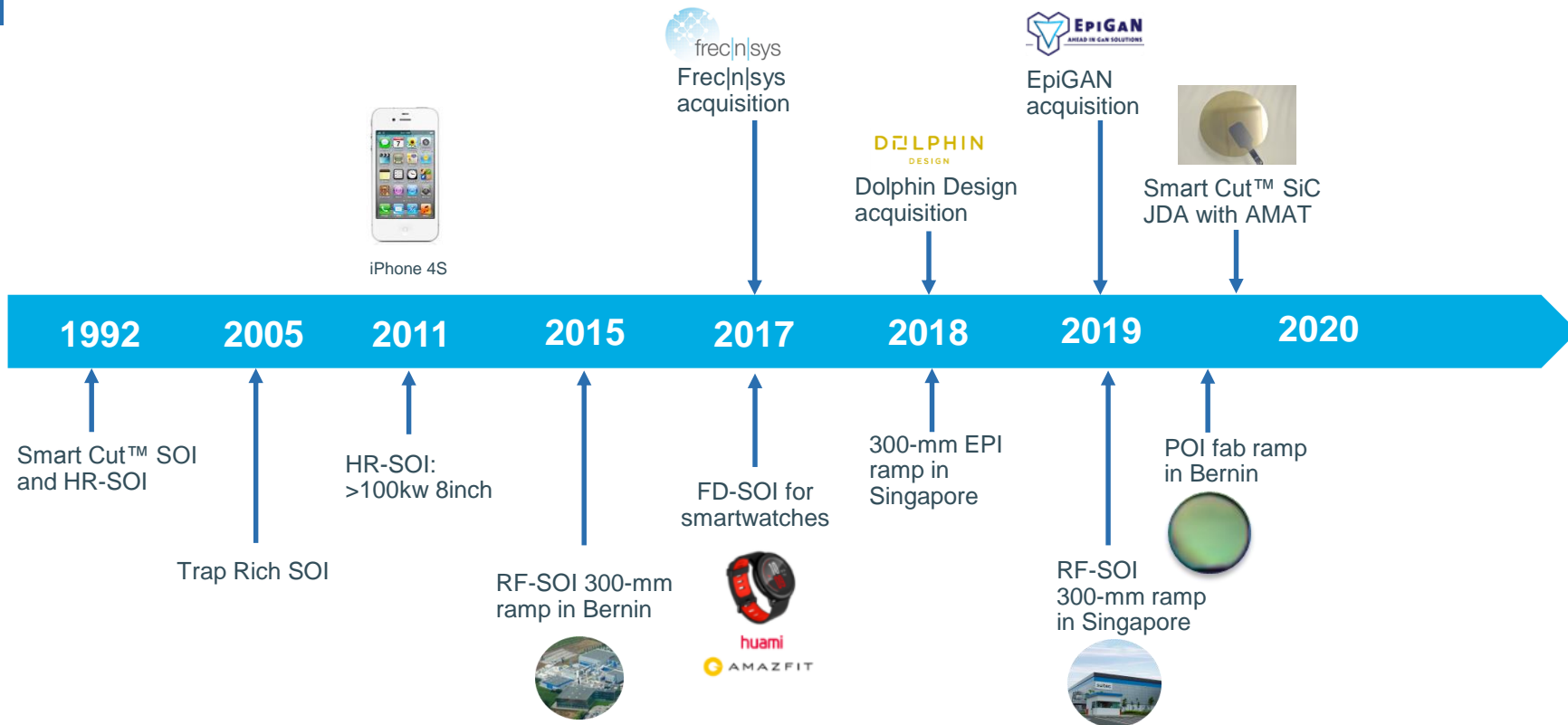
Remark: either GaN or RF-SOI or FD-SOI will be chosen for mmW FEM



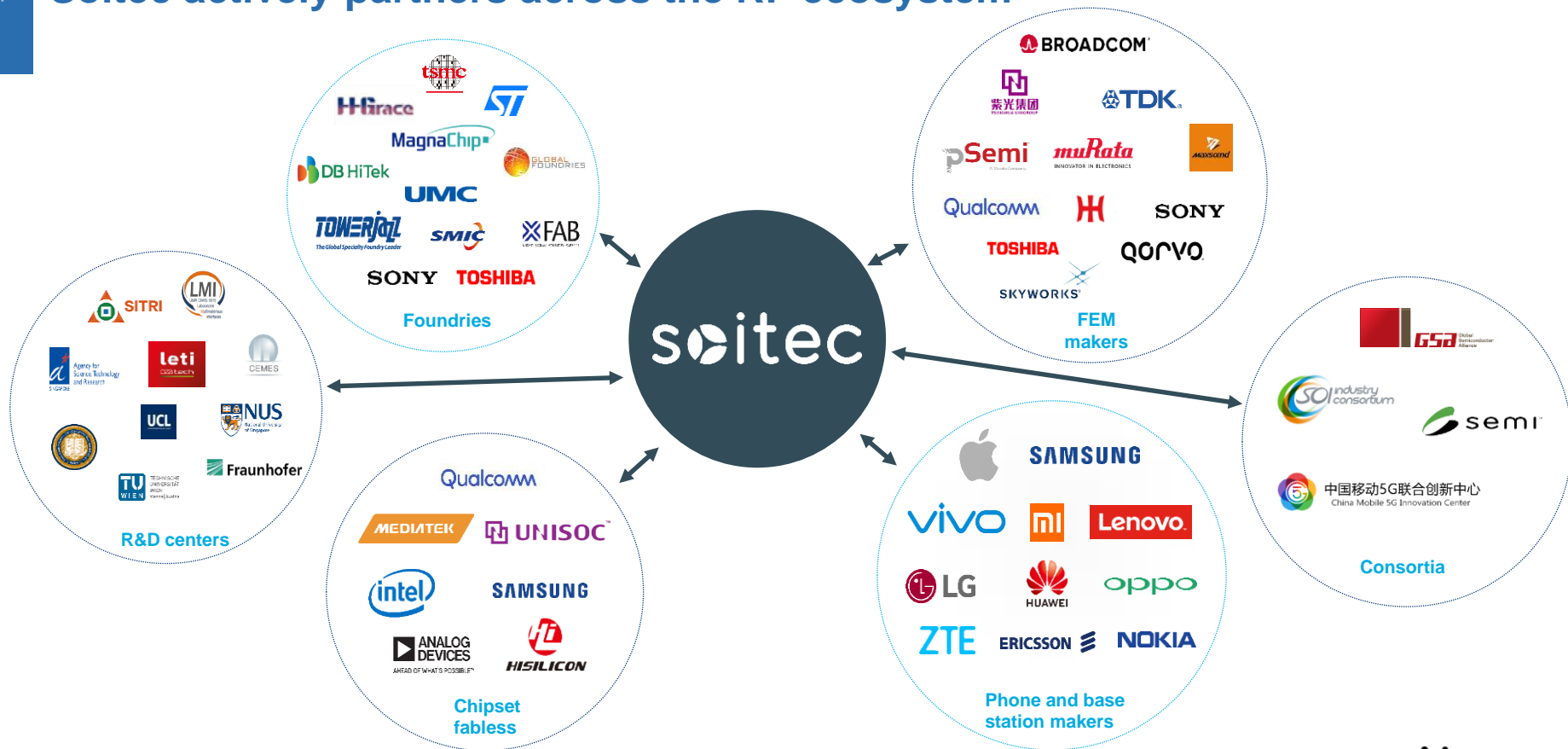
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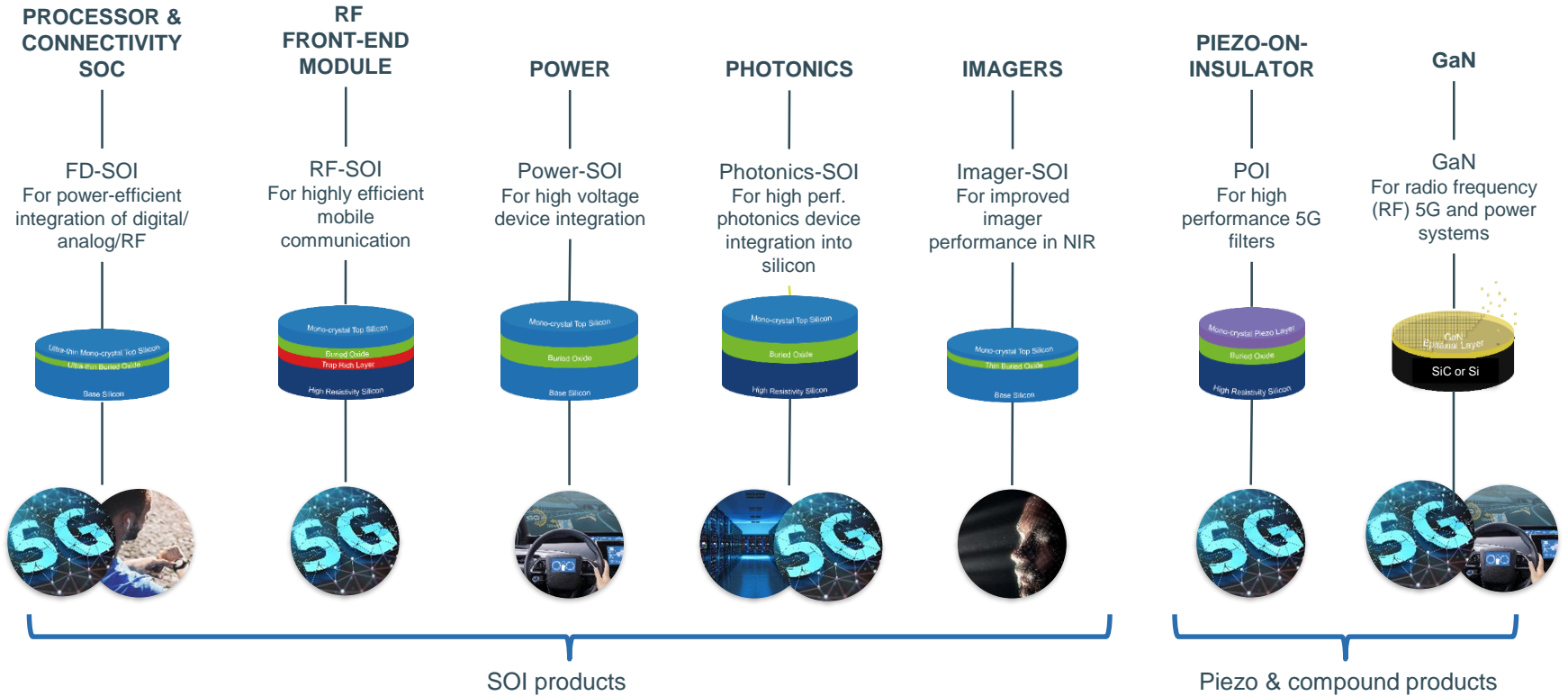
Soitec key milestones in serving the RF market



Soitec actively partners across the RF ecosystem



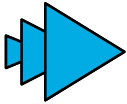




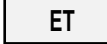
A broad product portfolio of engineered substrates



Soitec comprehensive product portfolio for 5G sub-6GHz handset RF FEM

- › RF-SOI mainstream technology for switch, LNA, tuner
- › POI target to become mainstream technology for filters

5G handset sub-6Ghz FEM key blocks

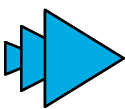



						
RF-SOI		✓	✓	✓		
POI					✓	
FD-SOI						✓

✓ Suitable solution

Soitec comprehensive product portfolio for 5G mmW handset RF FEM

- › Addressing different integration options
- › FD-SOI and RF-SOI (< 65 nm node) are both ideal technologies for mmW FEM
 - › Enable full FEM integration on single die critical for mmW to avoid interconnect losses
 - › Chipset leaders favor FD-SOI while FEM leaders favor RF-SOI
- › GaN delivers high performance for PA

5G handset mmW Transceivers key blocks

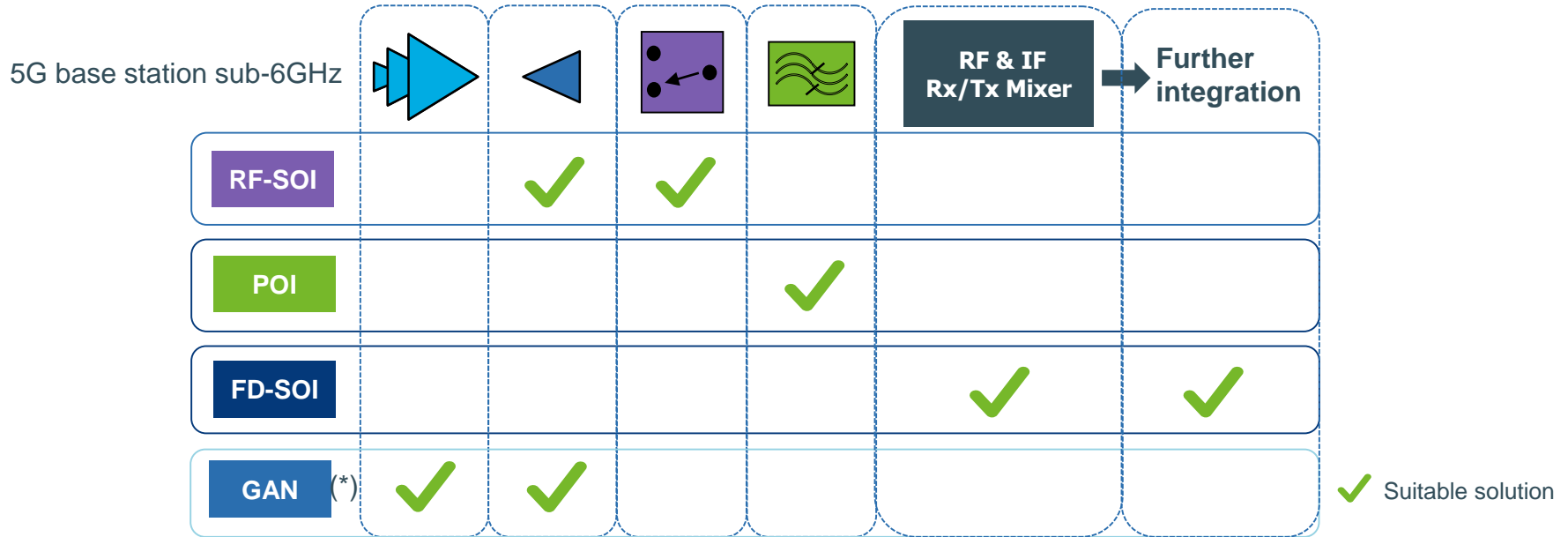
					RF & IF Rx/Tx Mixer	Further integration
FD-SOI	✓	✓	✓	✓	✓	✓
RF-SOI	✓	✓	✓	✓	✓	
GaN (*)	✓	✓	✓			

✓ Suitable solution

(*) : No public data available for GaN

Soitec comprehensive product portfolio for 5G sub-6GHz base stations

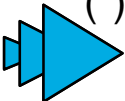
















› Soitec's product portfolio addresses most 5G base stations sub-6Ghz blocks



Soitec comprehensive product portfolio for 5G mmW small cells integration choices

- › GaN is the solution low complexity antenna
- › RF-SOI and FD-SOI are the solution for high complexity antenna

5G mmW small cells transceivers key blocks

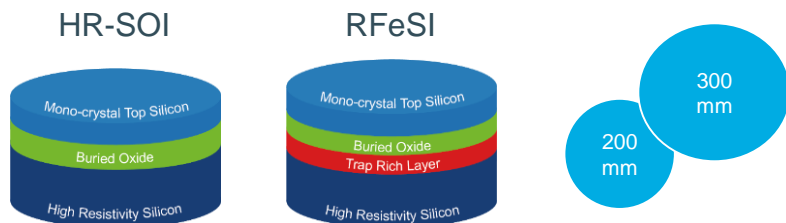
	 (*)				RF & IF Rx/Tx Mixer	ADC/DAC
GaN	 > 30dBm					
RF-SOI	 > 23dBm					
FD-SOI	 > 20dBm					

 Suitable solution

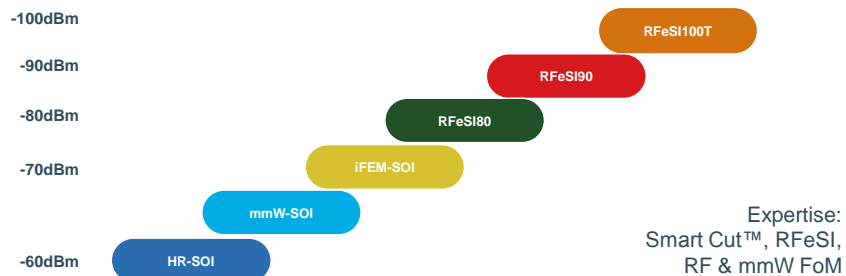
(*) : >30dBm for < 16 antenna, >23dBm for 128 antenna, >20dBm for >256 antenna

RF-SOI – standard for 4G and 5G RF FEM

Product description



A solid product roadmap



Global platform for 5G FEM

	SOITEC RF-SOI	HR Silicon Bulk	Silicon Germanium	MEMS	GaAs
Switch	+	=	-	+	+
Tuner	+	-	-	+	+
Power Amplifier	=	-	=	n.a	+
Cost	+	+	=	-	=
Integration / Area	+	+	+	-	-
Volume manufacturing 200/300mm	+	=	=	-	-

+ optimum = suitable - not suitable

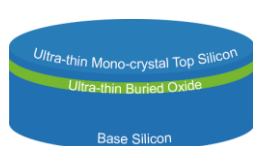
Source: Soitec analysis

Soitec manufacturing

Bernin 1 200mm	Bernin 2 300mm	Pasir Ris 300mm	Simgui 200mm
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FD-SOI for 5G mmW and system-on-chip (SoC)

Product description



FD-SOI offering

node	55nm	28nm	22nm	18nm	12nm	≤10nm
Status	Prod	Prod	Prod	Pilot	Dev	R&D
eMemory	No	Yes	Yes	Yes	Dev	R&D
RF perf.	Yes	Yes	Yes	Yes	Dev	R&D

Expertise :

- > Dolphin Design providing IP solution to fabless to master power management
- > FD-SOI body biasing deployed as main pillar
- > High resistive substrate applied to FD-SOI technology

Value proposition vs alternative technologies

	SOITEC FD-SOI	Planar bulk sub-40nm	Bulk FinFET sub-16nm	Silicon germanium
Best in class RF/mmW technology	+	=	=	+
System energy efficiency	+	=	+	=
Robustness (safety mission)	+	=	=	=
Cost	=	+	=	-
Integration SoC plateform	+	+	=	-

+ optimum = suitable - not suitable

Source: Soitec analysis

Soitec manufacturing

Bernin 2
300mm

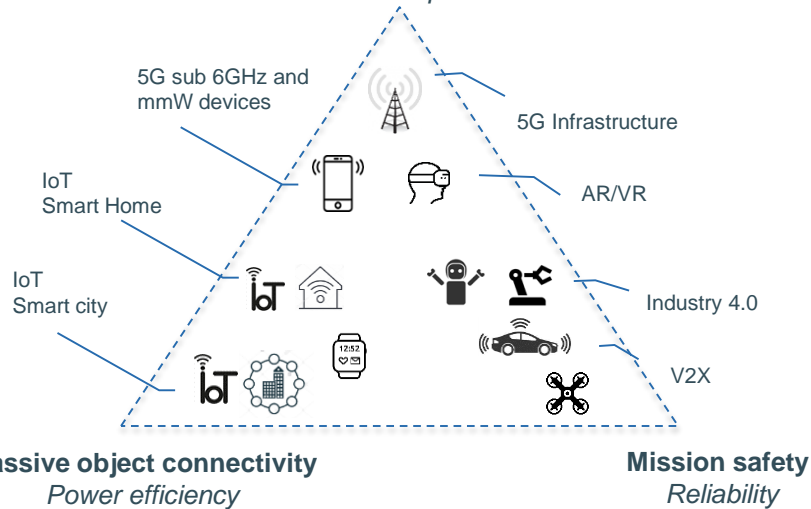
Pasir Ris
300mm

FD-SOI 5G applications

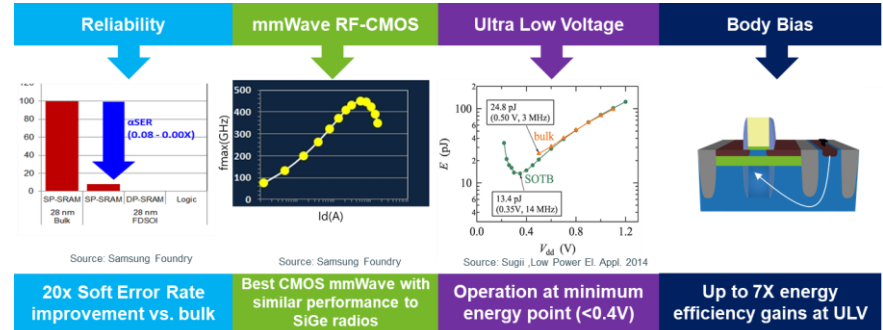
5G applications



Broadband access network & high data rate:
Best in class RF performances

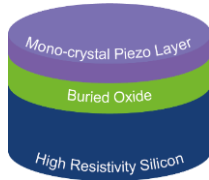


FD-SOI: differentiating performance at device level



Piezo-On-Insulator (POI): the ideal substrate for SAW filters

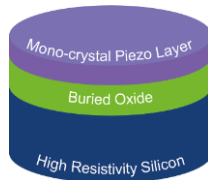
Product description



150 mm

Versatile product roadmap

● Device layer : Lithium tantalite or Lithium Niobate

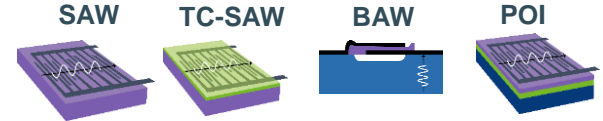


150 mm
200 mm

Expertise :
Smart Cut™, materials,
Acoustics FoM

200-mm to support filter pricing roadmap

Best value proposition for 5G filters



	SAW	TC-SAW	BAW	POI
Energy efficient	=	=	+	+
New 5G band (wide >200Mhz)	-	-	+	=
Temperature stability	-	+	=	+
Cost	+	=	-	=
Area	=	=	=	+
Volume manufacturing	+	+	=	+

+ optimum = suitable - not suitable

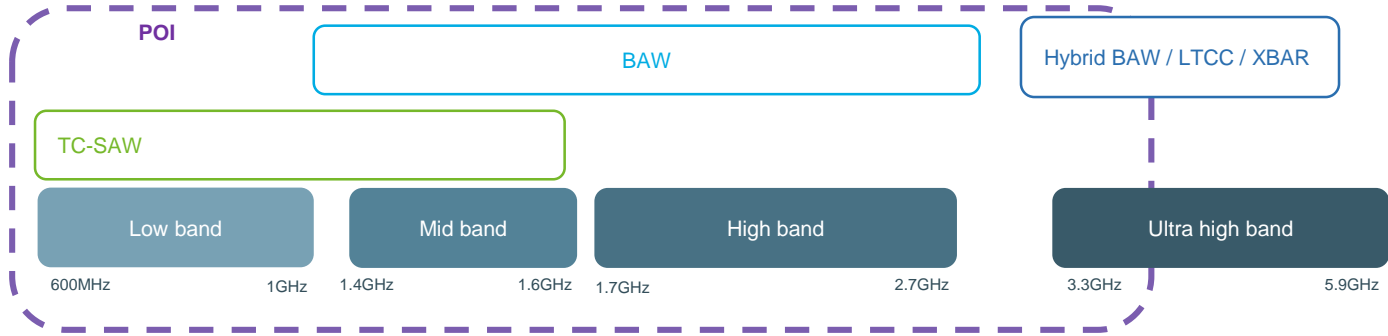
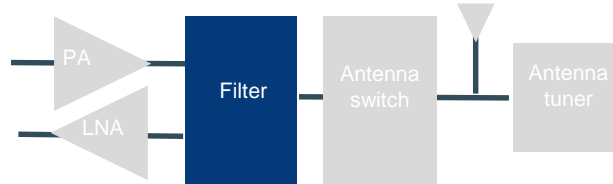
Source: Soitec analysis

Soitec manufacturing

Bernin 3
150mm

POI: a new paradigm addressing 5G

For all FEM in 5G smartphones
Ideal for 5G mid bands but not only!

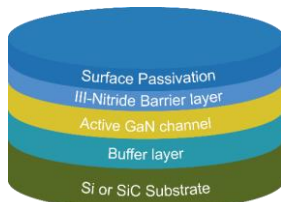


> 2017-2019: historical peak of new acoustics patents for 5G filters (> 600)

GaN for 5G

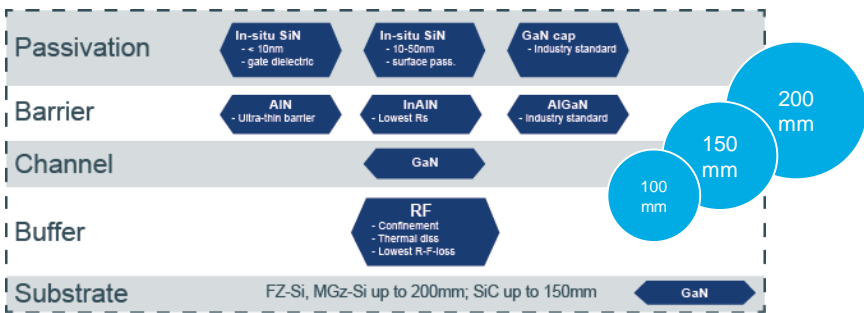
Product description

(Al,In,Ga)N Epi layer stack deposited on Silicon or Silicon Carbide wafer



Product roadmap

Soitec's toolbox for RF GaN product differentiation



Value proposition for base station PA

	LDMOS	GaN	SOI/CMOS
5G sub 6GHz PA	=	+	-
5G mmW PA >30dBm	-	+	-
5G sub 6GHz Cost	+	=	n.a
5G mmW PAs solution cost	n.a	=	+
Area	=	+	=

+ optimum = suitable - not suitable

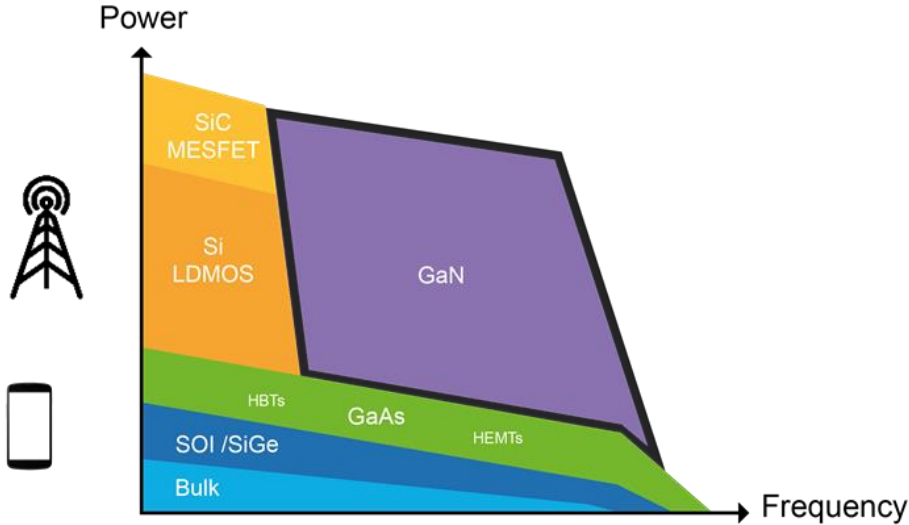
Source: Soitec, MACom analysis

Soitec manufacturing

Hasselt (Belgium)
GaN/Si up to 200mm; GaN/SiC up to 150-mm

GaN for 5G

RF – 5G

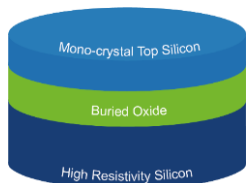


Source: Figure adapted from Analog Device 2017

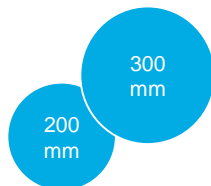
- › Cellular base stations (>5W power amplifier), MIMO antennas
 - › GaN - becoming mainstream for 4G / 5G <6GHz and mmW
- › Cellular handset (<3W Power amplifier)
 - › GaAs – mainstream technology today for 4G/ 5G <6Ghz
 - › GaN/Si – technology potential to enter the market

Photonics-SOI for 5G

Product description

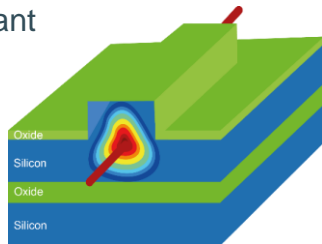


Bernin 1 & 2
200mm – 300mm

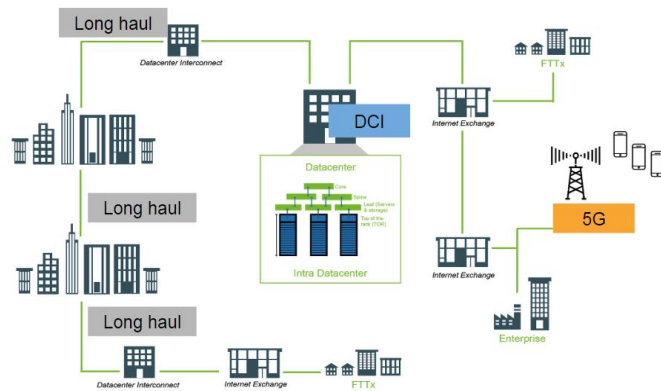


Product value proposition

- › Integration platform for complex optical function using CMOS fab
- › High speed modulation compliant
- › Low loss wave guide
- › Scalable solution for:
 - › Integration
 - › Performance
 - › Cost



5G applications 100/400 GbE for wireless backhaul



Silicon photonics main market is in data center (not considered as a 5G market segment)

Soitec manufacturing

Bernin 1
200mm

Bernin 2
300mm

Thank you

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 www.soitec.com

Disclaimer

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This document is provided for information purposes only. It is public information only.

The Company's business operations and financial position is described in the Company's registration document 2018-2019 registered by the Autorité des marchés financiers (the "AMF") on July 4th, 2019 under visa D.19-0649 (the "Document de Référence") and in the Company's FY'20 half-year report. Copies of the Document de Référence are available in French and English languages through the Company and may as well be consulted on the AMF's website (www.amf-france.org). The Document de Référence and the FY'20 half-year report can also be downloaded on the Company's website (www.soitec.com).

Your attention is drawn to the risk factors described in Chapter 2 of the Document de Référence. A review of these risk factors has been conducted after the closing of FY'20 first half and no new risk was found. This document contains summary information and should be read in conjunction with the Document de Référence and the FY'20 half-year report. In the event of a discrepancy between this document and the Document de Référence or the FY'20 half-year report, the Document de Référence or, as the case may be, the FY'20 half-year report, shall prevail.

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